

Product Overview

FGH75T65SQD: IGBT, 650 V, 75 A Field Stop Trench

For complete documentation, see the data sheet.

Using novel field stop IGBT technology, ON Semiconductor's new series of field stop 4th generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.

Features

- Maximum Junction Temperature: $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.6\text{ V(Typ.) @ } I_C = 75\text{ A}$
- 100% of the Parts Tested for ILM(1)
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- RoHS Compliant

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	V_{CES} Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Pack aged Diode	Package Type
FGH75T65SQD-F155	3.1866	Pb-free Halide free non AEC-Q and PPAP	Active	650			2	0.18	0.76		-	128	-	-	375		TO-247-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 1/23/2021